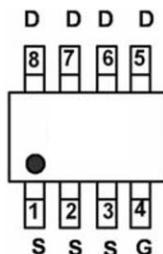
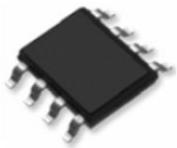


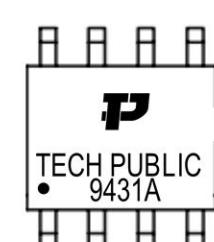
GENERAL FEATURES

BV_{DSS}	-20V
$R_{DS(ON)}$	22mΩ @ -4.5V (Max)
	25mΩ @ -3.3V (Max)
I_D	-7.5A

Package and Pin Configuration



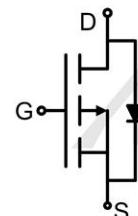
SOP-8 top view



Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Circuit diagram



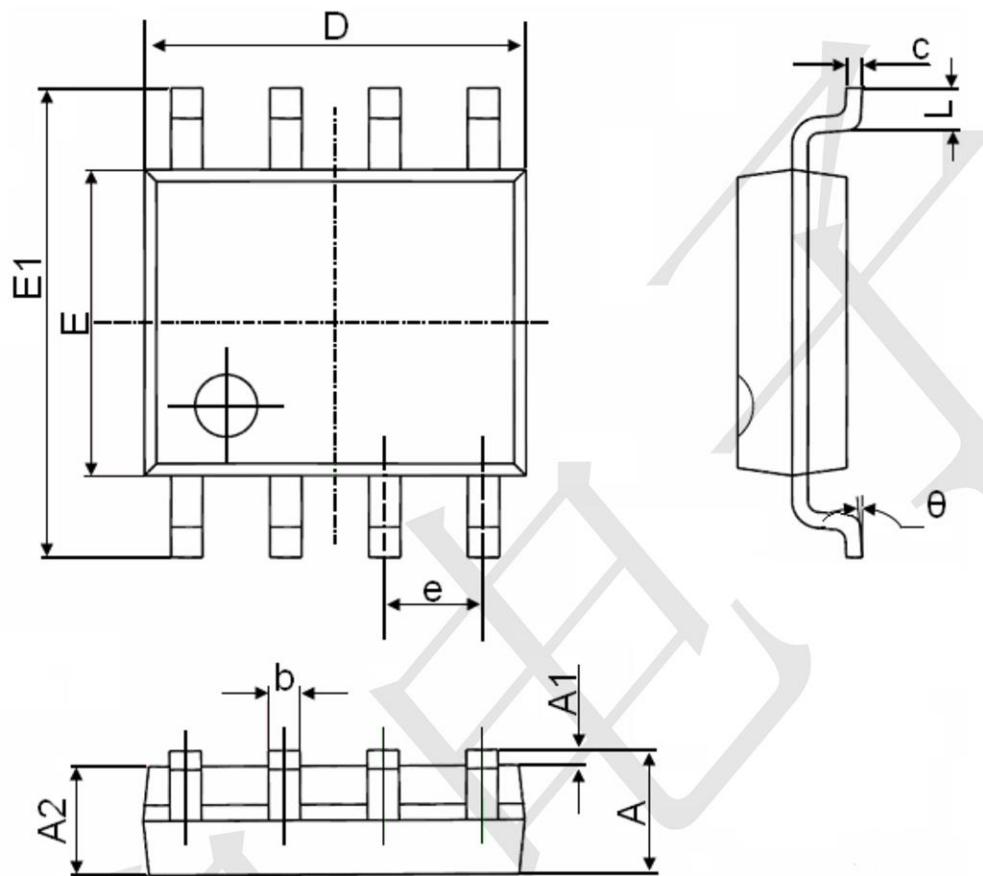
Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous ($T_A=25^\circ\text{C}$)	I_D	-7.5	A
Drain Current-Continuous ($T_A=70^\circ\text{C}$)		-6.4	
Drain Current-Pulsed ($T_A=25^\circ\text{C}$) ¹	I_{DM}	-28	A
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	3.1	W
Power Dissipation ($T_A=70^\circ\text{C}$)		2.4	W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	°C/W
Operating Junction Temperature Range	T_J	-50 To +150	°C
Storage Temperature Range	T_{STG}	-50 To +150	°C

Electrical Characteristics ($T_j=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_D=-250\mu\text{A}$	-20	-	-	V
Zero Gate Voltage Drain Current, $T_A=25^\circ\text{C}$	I_{DSS}	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Zero Gate Voltage Drain Current, $T_A=125^\circ\text{C}$		$V_{\text{DS}}=-12\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-100	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}, I_D=-250\mu\text{A}$	-0.4	-0.6	-1.0	V
Drain-Source On-State Resistance ²	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=-4.5\text{V}, I_D=7\text{A}$	-	-	22	$\text{m}\Omega$
		$V_{\text{GS}}=-3.3\text{V}, I_D=5\text{A}$	-	-	25	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_D=2\text{A}$	-	-	33	$\text{m}\Omega$
Dynamic and Switching Characteristics						
Total Gate Charge	Q_g	$V_{\text{DS}}=-10\text{V}, I_D=-5\text{A}, V_{\text{GS}}=-4.5\text{V}$	-	15.4	-	nC
Gate-Source Charge	Q_{gs}		-	2.0	-	
Gate-Drain Charge	Q_{gd}		-	3.6	-	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{GS}}=-4.5\text{V}, I_D=-1\text{A}, R_G=3.3\Omega, V_{\text{DD}}=10\text{V}$	-	8	-	nS
Rise Time	T_r		-	15.5	-	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		-	42	-	
Fall Time	T_f		-	10.5	-	
Input Capacitance	C_{iss}	$V_{\text{DS}}=-10\text{V}, V_{\text{GS}}=0\text{V}, F=1\text{MHz}$	-	1685	-	pF
Output Capacitance	C_{oss}		-	234	-	
Reverse Transfer Capacitance	C_{rss}		-	187	-	
Drain-Source Diode Characteristics and Maximum Ratings						
Source Drain Current (Body Diode)	I_{SD}	$T_A=25^\circ\text{C}$	-	-	-1.5	A
Diode Forward Voltage ²	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{SD}}=-5\text{A}, T_j=25^\circ\text{C}$	-	-0.85	-1.2	V

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°